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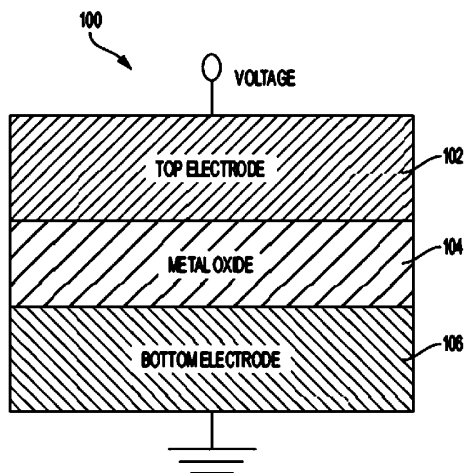
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(54) Title: DUAL DAMASCENE CROSSBAR ARRAY FOR DISABLING A DEFECTIVE RESISTIVE SWITCHING DEVICE IN THE ARRAY



(57) Abstract: Provided are method of fabricating a dual damascene crossbar array. The method includes forming a bottom electrode layer on a substrate and forming a first memory device on the bottom electrode layer. The method also includes forming a dual damascene structure on the first memory device, wherein the dual damascene structure includes a top electrode layer and a first via, wherein the first via is formed between the first memory device and the top electrode layer. Also provided are embodiments for the dual damascene crossbar and embodiments for disabling memory devices of the dual damascene crossbar array.

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